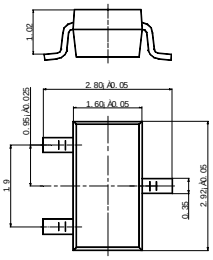
2SC2734 TRANSISTOR (NPN)

SOT-23-3L

1. BASE
2. EMITTER
3. COLLECTOR



FEATURES

Power dissipation

P_{CM}: 0.15 W (Tamb=25℃)

Collector current

I_{CM}: 0.05 A

Collector-base voltage

$V_{(BR)CBO}$: 20 V

Operating and storage junction temperature range

T_J, T_{stg}: -55℃ to +150℃

ELECTRICAL CHARACTERISTICS (Tamb=25℃ unless otherwise specified)

Parameter	Symbol	Test conditions	MIN	MAX	UNIT
Collector-base breakdown voltage	$V_{(BR)CBO}$	Ic=10μA, I_E=0	20		V
Collector-emitter breakdown voltage	$V_{(BR)CEO}$	Ic= 1mA, I_B=0	11		V
Emitter-base breakdown voltage	$V_{(BR)EBO}$	I_E= 10μA, I_C=0	3		V
Collector cut-off current	I_{CBO}	V_{CB}= 10 V , I_E=0		0.5	μA
DC current gain	h_{FE}	V_{CE}= 10V, I_C= 5mA	20	200	
Collector-emitter saturation voltage	V_{CE}(sat)	I_C=10mA, I_B= 5mA		0.7	V
Transition frequency	f_T	V_{CE}=10V, I_C= 10mA	1.4		GHz
Collector output capacitance	C_{ob}	V_{CB}=10V, I_E=0, f=1MHz		1.5	pF
Noise figure	NF	V_{CC}=6V, I_c=2mA, f_{out}=30MHz f=900MHZ, f_{osc}= 930MHz		12	dB

Marking	**GC**